

In re: Deok-Hyung Lee et al.  
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**In the Claims:**

1. (Original) A field effect transistor comprising:  
a fin extending from a substrate, the fin including an upper portion remote from the substrate and sidewalls that extend between the upper portion and the substrate;  
a channel region in the fin;  
a gate electrode adjacent the channel region and crossing over the fin;  
a gate insulation layer interposed between the gate electrode and the fin; and  
source/drain regions formed at both sides of the gate electrode, wherein the channel region at the upper portion of the fin is doped higher than sidewalls of the fin.
2. (Original) The transistor of Claim 1, wherein the channel region comprises:  
a first layer in the upper portion of the fin; and  
a second layer beneath the first layer, wherein the second layer is lightly doped relative to the first layer.
3. (Original) The transistor of Claim 1;  
wherein the substrate includes a semiconductor layer and an insulation layer on the semiconductor layer; and  
wherein the fin is on the insulation layer.
4. (Original) The transistor of Claim 1:  
wherein the substrate is a bulk semiconductor layer; and  
wherein the semiconductor layer extends vertically to form the fin.
5. (Original) The transistor of Claim 4, further comprising an insulation layer disposed between the gate electrode and the semiconductor layer at a periphery of the fin.

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6. (Original) The transistor of Claim 4, further comprising a punch-through stop layer beneath the channel region having a higher doping concentration than the second layer.

7. (Original) The transistor of Claim 2, wherein the second layer has uniform concentration in the channel region.

8-12. (Canceled)

13. (Original) An integrated circuit field effect transistor comprising:  
an integrated circuit substrate;  
a fin that projects away from the integrated circuit substrate, extends along the integrated circuit substrate and includes a top that is remote from the integrated circuit substrate;  
a channel region in the fin that is doped a predetermined conductivity type and having a higher doping concentration of the predetermined conductivity type adjacent the top than remote from the top;  
a source region and a drain region in the fin on respective opposite sides of the channel region; and  
an insulated gate electrode that extends across the fin, adjacent the channel region.

14. (Original) The integrated circuit field effect transistor according to Claim 13 wherein the channel region is uniformly doped the predetermined conductivity type at a first doping concentration except for being doped the predetermined conductivity type at a second doping concentration that is higher than the first doping concentration adjacent the top.

15. (Original) The integrated circuit field effect transistor according to Claim 13 wherein the channel region comprises a first region of the predetermined conductivity type adjacent the top and a second region of the predetermined

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conductivity type remote from the top, wherein the first region is more heavily doped than the second region.

16. (Original) The integrated circuit field effect transistor according to Claim 13 wherein the fin also includes first and second sidewalls that extend between the top and the substrate and wherein the channel region has the higher doping concentration of the predetermined conductivity type directly beneath the top, from the first sidewall to the second sidewall.

17. (Original) The integrated circuit field effect transistor according to Claim 13:  
wherein the integrated circuit substrate is a bulk semiconductor substrate such that the bulk semiconductor substrate includes a projection that defines the fin;  
the integrated circuit field effect transistor further comprising a region of the predetermined conductivity type in the bulk semiconductor substrate beneath the fin.

18. (Original) The integrated circuit field effect transistor according to Claim 13 wherein the integrated circuit substrate comprises an insulating layer on a substrate and wherein the fin is on the insulating layer, opposite the substrate.

19. (Original) The integrated circuit field effect transistor according to Claim 13 further comprising:  
a capacitor connected to the source region.

20. (Original) The integrated circuit field effect transistor according to Claim 13 further comprising:  
a bit line connected to the drain region.

21-22. (Canceled)